

AMENDMENTS TO THE CLAIMS:

The following listing of claims replaces all prior listings, and all prior versions, of claims in the application.

LISTING OF CLAIMS:

1.-163. (Cancelled).

164. (Previously presented) A metal-polishing liquid which comprises an oxidizing agent, an oxidized-metal etchant, a protective film-forming agent, a dissolution promoter for the protective film-forming agent, and water, wherein the dissolution promoter is a surfactant, said surfactant being at least one selected from the group consisting of esters, ethers, polysaccharides, salts of amino acids, polycarboxylic acids, salts of polycarboxylic acids, vinyl polymers, sulfonic acids, sulfonates, and amides.

165. (Previously presented) The metal-polishing liquid according to claim 164, wherein at least a part of the protective film-forming agent is solid, having a mean particle size of at most 100 μm .

166. (Previously presented) The metal-polishing liquid according to claim 164, further comprising abrasive grains.

167. (Previously presented) A method for producing a metal-polishing liquid, comprising a step of diluting the metal-polishing liquid material of claim 160 with a diluent.

168. (Previously presented) A method for producing a metal-polishing liquid of claim 164, comprising a step of diluting a metal-polishing liquid material comprising at least one ingredient of an ingredient group consisting of the oxidizing agent, the oxidized-metal etchant, the protective film-forming agent and the dissolution promoter for the protective film-forming agent, with an aqueous solution for dilution of at least one ingredient of the ingredient group.

169. (Previously presented) A method for producing a metal-polishing liquid of claim 164, which comprises a step of mixing the following in any desired order:

a first constituent element that contains at least one ingredient of an ingredient group consisting of said oxidizing agent, said oxidized-metal etchant, said protective film-forming agent and said dissolution promoter for the protective film-forming agent,

a second constituent element that contains at least one of the other ingredients of the ingredient group, and

a diluent,

wherein at least one of the first constituent element and the second constituent element includes said dissolution promoter for the protective film-forming agent.

170. (Previously presented) The method for producing a metal-polishing liquid according to claim 169, wherein the diluent is water or an aqueous diluent solution.

171. (Previously presented) The method for producing a metal-polishing liquid according to claim 169, wherein the first constituent element comprises the oxidizing agent, and the second constituent element comprises the oxidized-metal etchant, the protective film-forming agent and the dissolution promoter.

172. (Previously presented) The method for producing a metal-polishing liquid according to claim 169, wherein the first constituent element further comprises the protective film-forming agent and the dissolution promoter.

173. (Previously presented) The method for producing a metal-polishing liquid as claimed in claim 169, wherein in the mixing step, the oxidizing agent and the oxidizing agent-containing mixture are kept at a temperature of at most 40°C.

174. (Previously presented) The method for producing a metal-polishing liquid as claimed in claim 169, wherein at least a part of the protective film-forming agent is solid, having a mean particle size of at most 100 μm , and is dissolved or dispersed in the metal-polishing liquid in the mixing step.

175. – 179. (Cancelled).

180. (Previously presented) The method for producing a metal-polishing liquid according to claim 167, wherein the diluent is water or an aqueous diluent solution.

181. – 184. (Cancelled).

185. (Previously presented) The metal-polishing liquid according to claim 164, wherein the protective film-forming agent is at least one selected from the group consisting of ammonia, amines, amino acids, imines, azoles, mercaptans, polysaccharides, salts of amino acids, polycarboxylic acids and their salts, and vinyl polymers.